

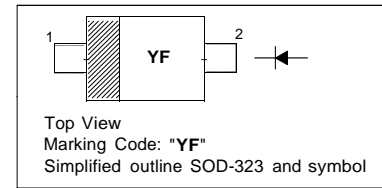
## SILICON SCHOTTKY BARRIER DIODE

### Features

- Low forward voltage drop and suitable for high efficiency rectifying
- Ultra small resin package is suitable for high density surface mounting and high speed assembly

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	30	V
Mean Rectifying Current	$I_O$	100	mA
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine Wave)	$I_{FSM}$	1	A
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	0.44	V
Reverse Current at $V_R = 30\text{ V}$	$I_R$	50	$\mu\text{A}$

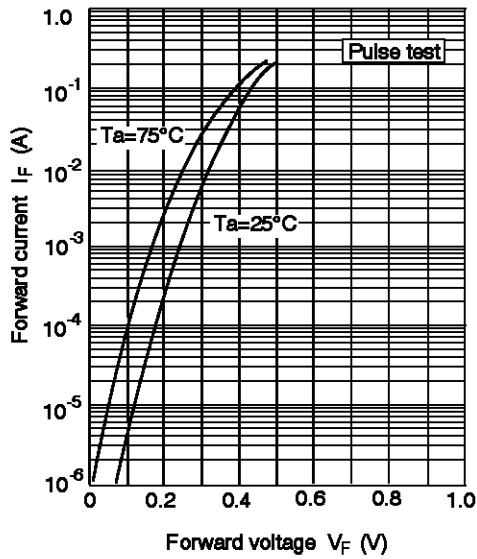


Fig.1 Forward current Vs. Forward voltage

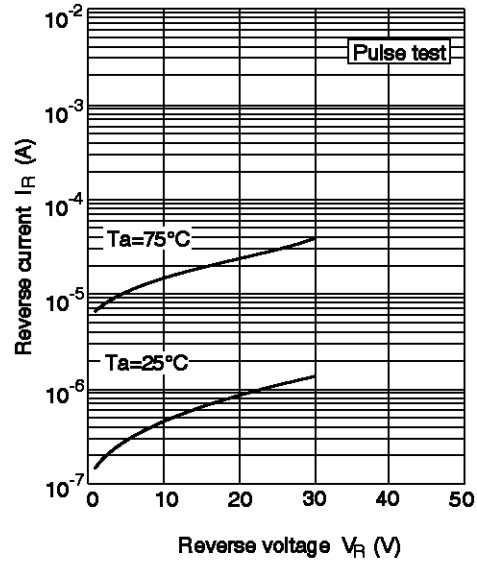


Fig.2 Reverse current Vs. Reverse voltage

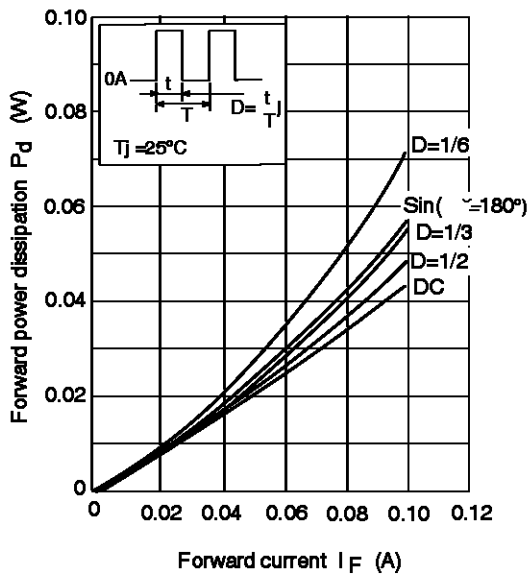


Fig.3 Forward power dissipation Vs. Forward current

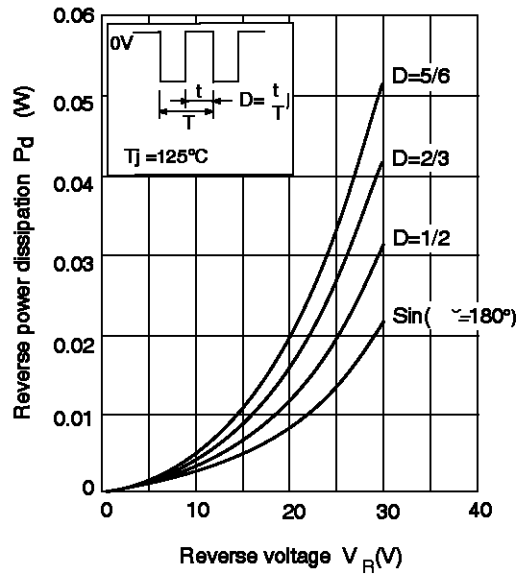


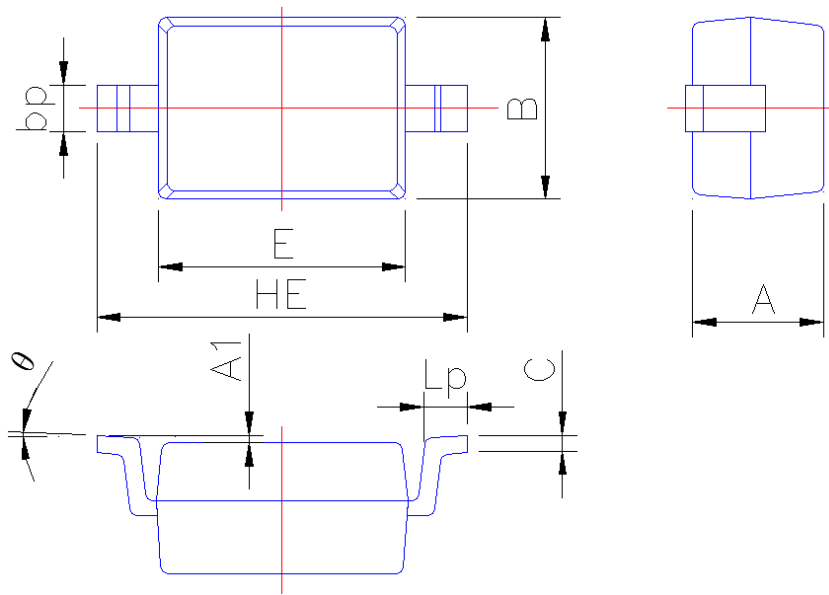
Fig.4 Reverse power dissipation Vs. Reverse voltage



**PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°